

# DATA SHEET

## **PDTC143E series**

**NPN resistor-equipped transistors;**

**R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$**

Product specification  
Supersedes data of 1999 Apr 15

2003 Apr 10

## NPN resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

## PDTC143E series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	50	V
I <sub>O</sub>	output current (DC)	–	100	mA
R1	bias resistor	4.7	–	k $\Omega$
R2	bias resistor	4.7	–	k $\Omega$

### DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	PNP COMPLEMENT
	PHILIPS	EIAJ		
PDTC143EE	SOT416	SC-75	02	PDTA143EE
PDTC143EK	SOT346	SC-59	02	PDTA143EK
PDTC143EM	SOT883	SC-101	E1	PDTA143EM
PDTC143ES	SOT54 (TO-92)	SC-43	TC143E	PDTA143ES
PDTC143ET	SOT23	–	*02 <sup>(1)</sup>	PDTA143ET
PDTC143EU	SOT323	SC-70	*02 <sup>(1)</sup>	PDTA143EU

### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

NPN resistor-equipped transistors;  
 R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTC143E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC143ES		1 2 3	base collector emitter
PDTC143EE PDTC143EK PDTC143ET PDTC143EU		1 2 3	base emitter collector
PDTC143EM		1 2 3	base emitter collector

NPN resistor-equipped transistors;  
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## PDTC143E series

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	10	V
V <sub>I</sub>	input voltage positive negative		–	+30	V
			–	–10	V
I <sub>O</sub>	output current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	100	mA
P <sub>tot</sub>	total power dissipation SOT54 SOT23 SOT346 SOT323 SOT416 SOT883	T <sub>amb</sub> ≤ 25 °C			
		note 1	–	500	mW
		note 1	–	250	mW
		note 1	–	250	mW
		note 1	–	200	mW
		note 1	–	150	mW
	notes 2 and 3	–	250	mW	
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Notes**

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient SOT54 SOT23 SOT346 SOT323 SOT416 SOT883	in free air		
		note 1	250	K/W
		note 1	500	K/W
		note 1	500	K/W
		note 1	625	K/W
		note 1	833	K/W
	notes 2 and 3	500	K/W	

**Notes**

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

NPN resistor-equipped transistors;  
 $R1 = 4.7 \text{ k}\Omega$ ,  $R2 = 4.7 \text{ k}\Omega$

PDTC143E series

### CHARACTERISTICS

$T_{\text{amb}} = 25 \text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{\text{CBO}}$	collector-base cut-off current	$V_{\text{CB}} = 50 \text{ V}$ ; $I_{\text{C}} = 0$	–	–	100	nA
$I_{\text{CEO}}$	collector-emitter cut-off current	$V_{\text{CE}} = 30 \text{ V}$ ; $I_{\text{B}} = 0$	–	–	1	$\mu\text{A}$
		$V_{\text{CE}} = 30 \text{ V}$ ; $I_{\text{B}} = 0$ ; $T_{\text{j}} = 150 \text{ }^\circ\text{C}$	–	–	50	$\mu\text{A}$
$I_{\text{EBO}}$	emitter-base cut-off current	$V_{\text{EB}} = 5 \text{ V}$ ; $I_{\text{C}} = 0$	–	–	900	$\mu\text{A}$
$h_{\text{FE}}$	DC current gain	$V_{\text{CE}} = 5 \text{ V}$ ; $I_{\text{C}} = 10 \text{ mA}$	30	–	–	
$V_{\text{CEsat}}$	collector-emitter saturation voltage	$I_{\text{C}} = 10 \text{ mA}$ ; $I_{\text{B}} = 0.5 \text{ mA}$	–	–	150	mV
$V_{\text{i(off)}}$	input-off voltage	$I_{\text{C}} = 100 \text{ }\mu\text{A}$ ; $V_{\text{CE}} = 5 \text{ V}$	–	1.1	0.5	V
$V_{\text{i(on)}}$	input-on voltage	$I_{\text{C}} = 20 \text{ mA}$ ; $V_{\text{CE}} = 0.3 \text{ V}$	2.5	1.9	–	V
R1	input resistor		3.3	4.7	6.1	$\text{k}\Omega$
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
$C_{\text{c}}$	collector capacitance	$I_{\text{E}} = i_{\text{e}} = 0$ ; $V_{\text{CB}} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	–	–	2.5	pF

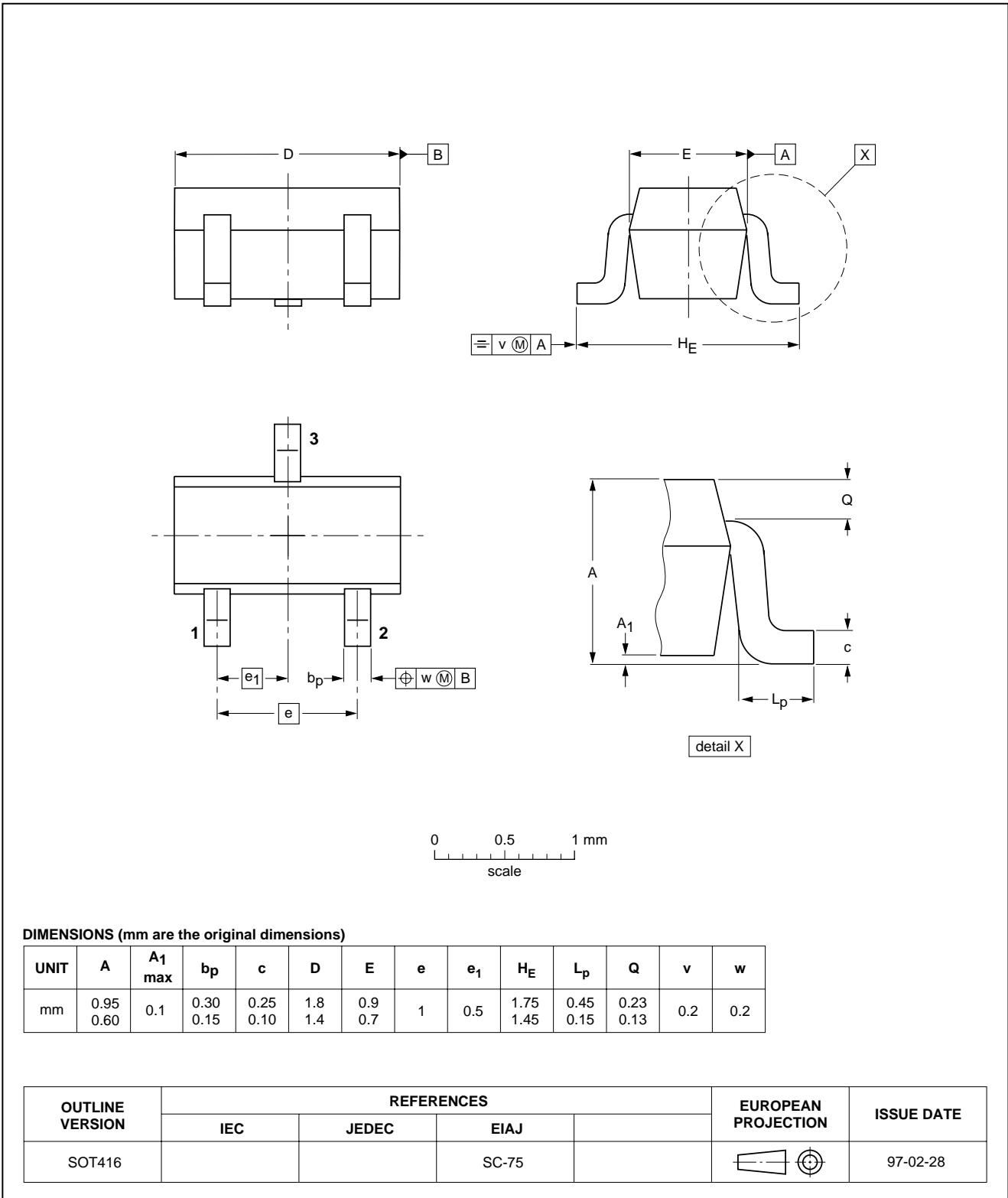
NPN resistor-equipped transistors;  
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTC143E series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT416

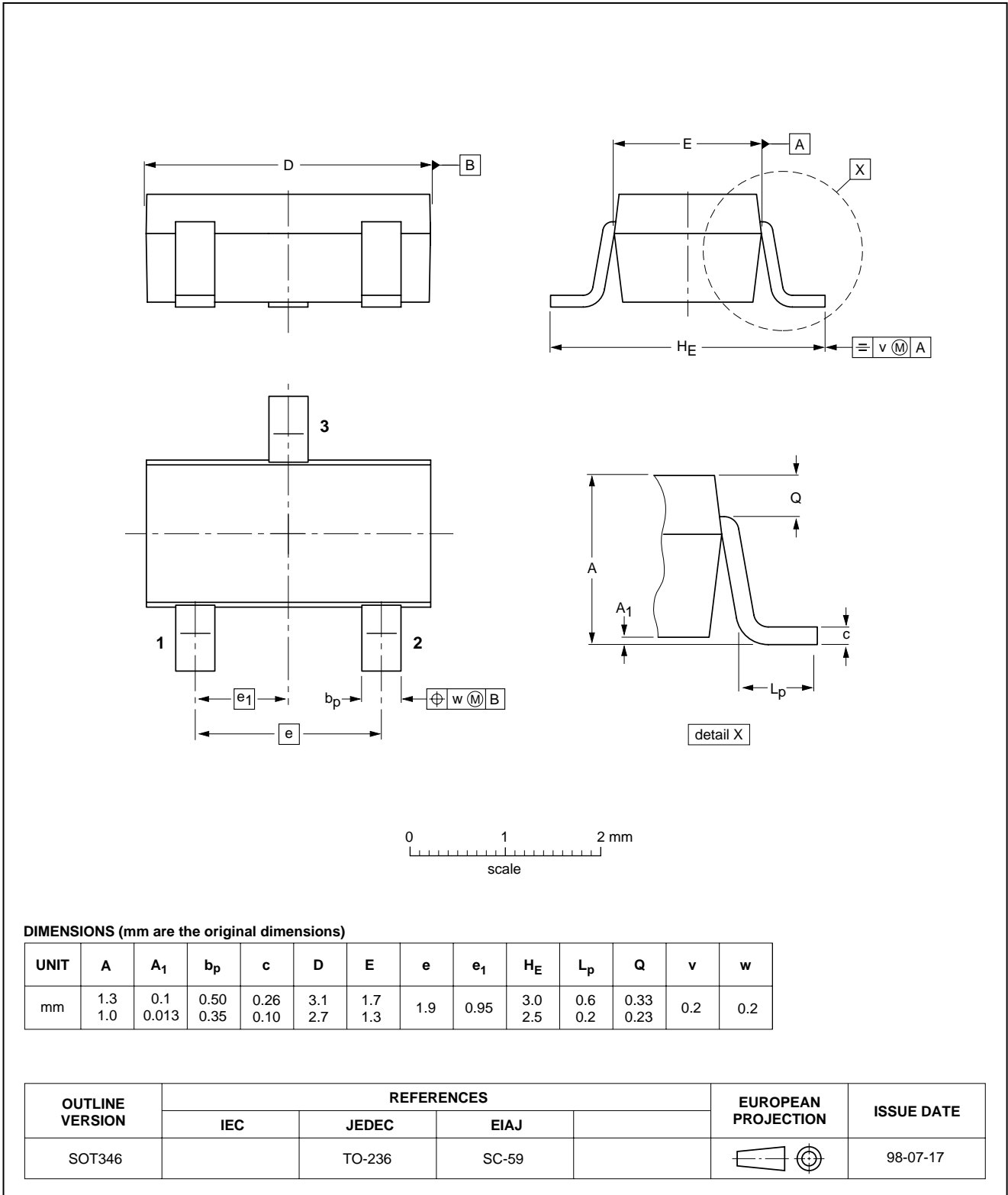


NPN resistor-equipped transistors;  
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTC143E series

Plastic surface mounted package; 3 leads

SOT346

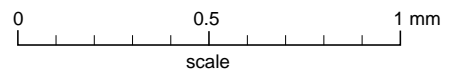
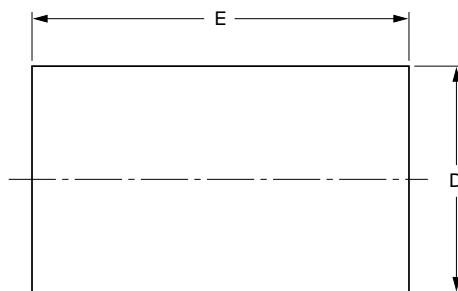
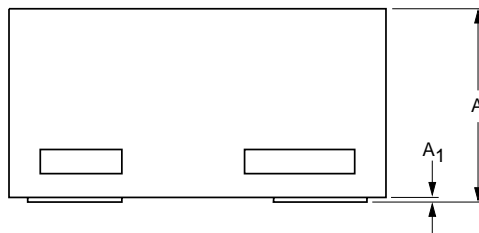
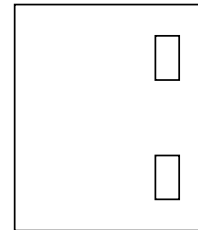
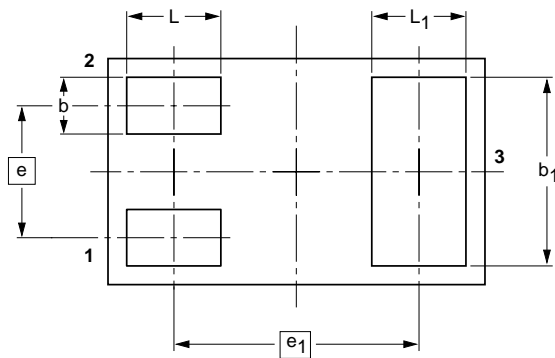


NPN resistor-equipped transistors;  
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTC143E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



DIMENSIONS (mm are the original dimensions)

UNIT	A <sup>(1)</sup>	A <sub>1</sub> max.	b	b <sub>1</sub>	D	E	e	e <sub>1</sub>	L	L <sub>1</sub>
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT883			SC-101			03-02-05- 03-04-03

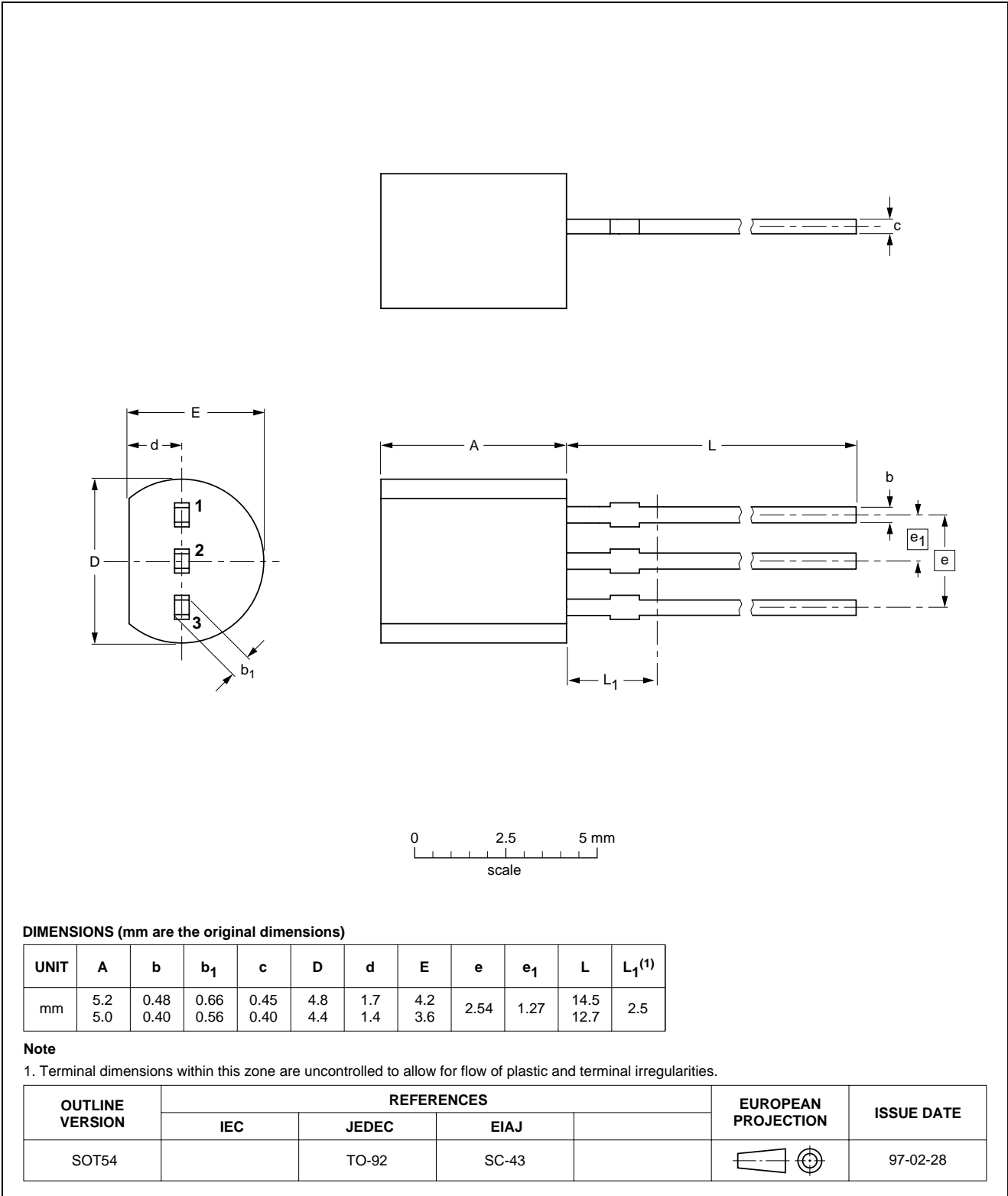


NPN resistor-equipped transistors;  
 R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTC143E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

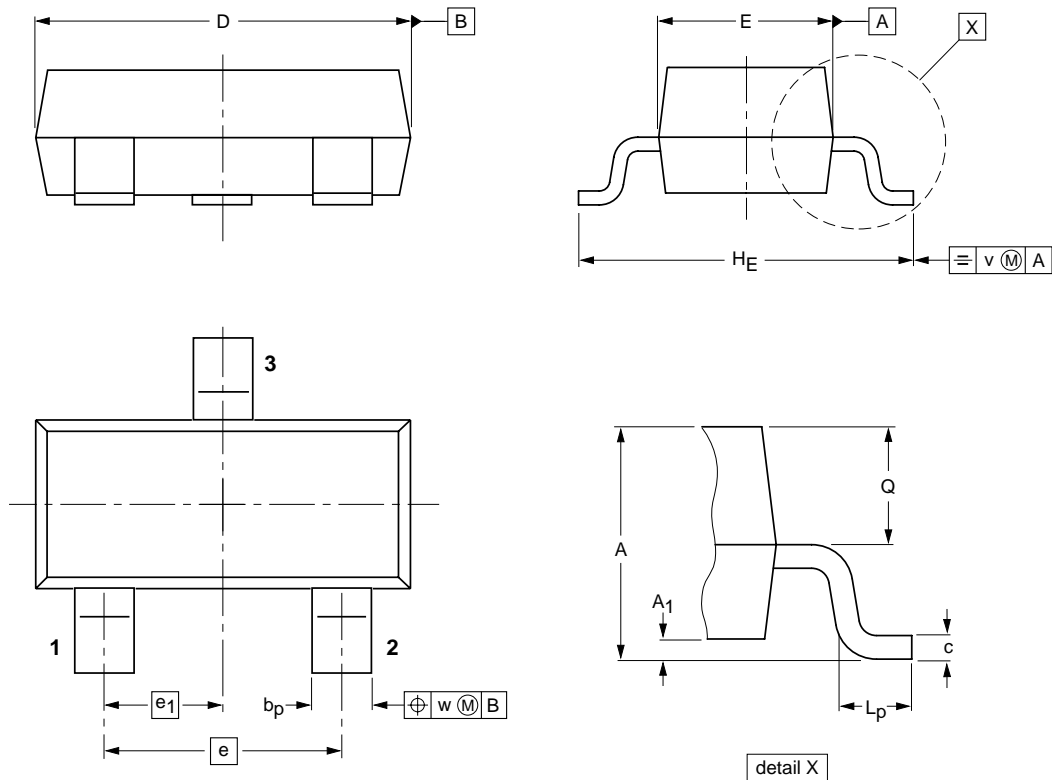


NPN resistor-equipped transistors;  
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTC143E series

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

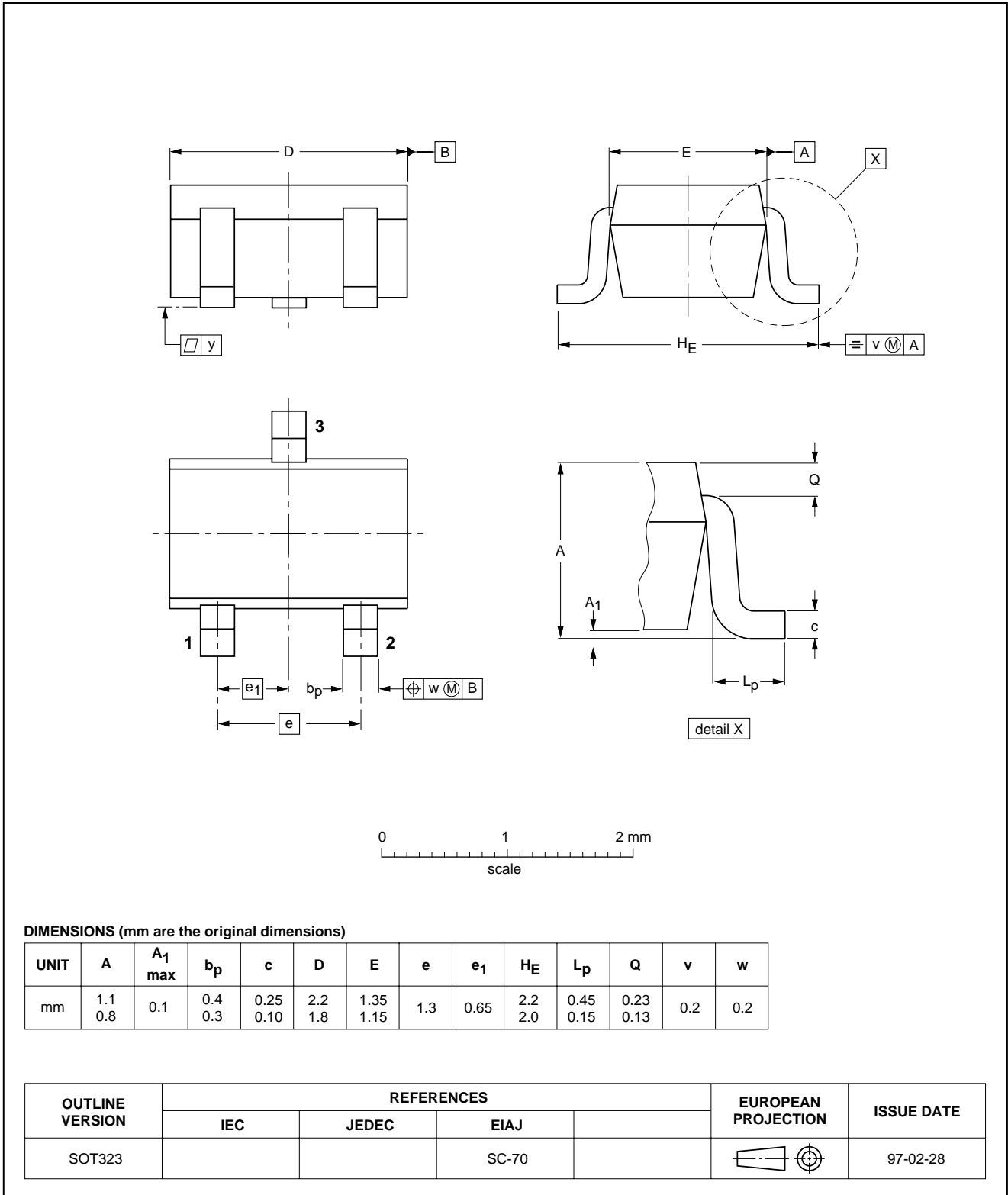
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28- 99-09-13

NPN resistor-equipped transistors;  
R1 = 4.7 kΩ, R2 = 4.7 kΩ

PDTC143E series

Plastic surface mounted package; 3 leads

SOT323



NPN resistor-equipped transistors;  
R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

PDTC143E series

#### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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**NOTES**

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